

MA3J744

Silicon epitaxial planar type

For super-high speed switching circuit

For small current rectification

Features

- Small S-mini type package allowing high-density mounting
- Allowing to rectify under ($I_{F(AV)} = 200$ mA) condition

Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	V_R	30	V
Repetitive peak reverse voltage	V_{RRM}	30	V
Average forward current	$I_{F(AV)}$	200	mA
Peak forward current	I_{FM}	300	mA
Non-repetitive peak forward surge current*	I_{FSM}	1	A
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

Note) * : The peak-to-peak value in one cycle of 50 Hz sine-wave (non-repetitive)

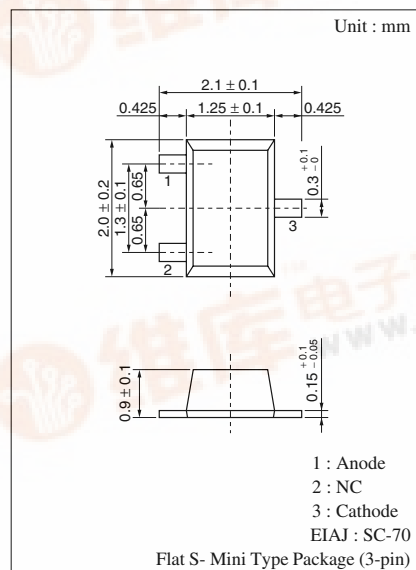
Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current (DC)	I_R	$V_R = 30$ V			50	μA
Forward voltage (DC)	V_F	$I_F = 200$ mA			0.55	V
Terminal capacitance	C_t	$V_R = 0$ V, $f = 1$ MHz		30		pF
Reverse recovery time*	t_{rr}	$I_F = I_R = 100$ mA $I_{rr} = 10$ mA, $R_L = 100$ Ω		3		ns

Note) 1. Schottky barrier diode is sensitive to electric shock (static electricity, etc.). Due attention must be paid on the charge of a human body and the leakage of current from the operating equipment.

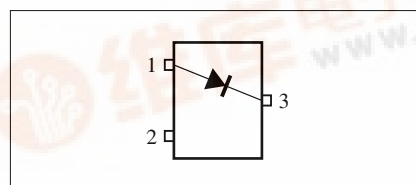
2. Rated input/output frequency: 1 000 MHz

3. *: t_{rr} measuring instrument



Marking Symbol: M1M

Internal Connection



Bias Application Unit N-50BU

